

18. (Amended) A method of manufacturing a semiconductor device comprising steps of:
forming a semiconductor layer on an insulating surface;
forming an insulating film on said semiconductor layer;
forming a first electrode comprising a laminate structure of a first conductive layer with a first width and a second conductive layer on said insulating film;
etching said second conductive layer to form a second electrode comprising a laminate structure of said first conductive layer with said first width and said second conductive layer with a second width;
adding an impurity element to said semiconductor layer using said second electrode as a mask to form a high concentration impurity region;
adding said impurity element to said semiconductor layer of the second electrode through said first conductive layer of the second electrode using the second conductive layer as a mask to form a low concentration impurity region; and
etching said first conductive layer to form a third electrode comprising a laminate structure of said first conductive layer with a third width and said second conductive layer with said second width. --